

Yuji Yamamoto

List of Publications by Year in descending order

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papers

381
citations

840776

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25
all docs

25
docs citations

25
times ranked

390
citing authors

#	ARTICLE	IF	CITATIONS
1	Threading Dislocation Reduction of Ge by Introducing a SiGe/Ge Superlattice. ECS Journal of Solid State Science and Technology, 2021, 10, 034005.	1.8	3
2	CMOS-Compatible Bias-Tunable Dual-Band Detector Based on GeSn/Ge/Si Coupled Photodiodes. ACS Photonics, 2021, 8, 2166-2173.	6.6	36
3	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. Physical Review Materials, 2020, 4, .	2.4	20
4	Threading Dislocation Reduction of Ge by Introducing a SiGe/Ge Superlattice. ECS Transactions, 2020, 98, 185-194.	0.5	3
5	Threading Dislocation Reduction of Ge by Introducing a SiGe/Ge Superlattice. ECS Meeting Abstracts, 2020, MA2020-02, 1763-1763.	0.0	1
6	Synthesis of Armchair Graphene Nanoribbons on Germanium-on-Silicon. Journal of Physical Chemistry C, 2019, 123, 18445-18454.	3.1	12
7	Process Effects on the Noise Performance of SiGe/Si Multi Quantum Well Thermistor. ECS Transactions, 2019, 93, 105-108.	0.5	1
8	Group IV Heteroepitaxy for Advanced Electronic Devices Integrated in BiCMOS Technology. ECS Transactions, 2019, 93, 1-5.	0.5	0
9	Self-Ordered Ge Nanodot Fabrication by Using Reduced Pressure Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, P190-P195.	1.8	4
10	CVD Synthesis of Armchair Graphene Nanoribbons on Ge/Si(001). ECS Transactions, 2019, 93, 133-136.	0.5	2
11	Influence of Annealing Condition on Threading Dislocation Density of Ge Grown by RPCVD. ECS Transactions, 2019, 93, 87-90.	0.5	1
12	Alignment control of self-ordered three dimensional SiGe nanodots. Semiconductor Science and Technology, 2018, 33, 114014.	2.0	5
13	Influence of annealing conditions on threading dislocation density in Ge deposited on Si by reduced pressure chemical vapor deposition. Semiconductor Science and Technology, 2018, 33, 124007.	2.0	19
14	Photoluminescence from GeSn nano-heterostructures. Nanotechnology, 2018, 29, 415702.	2.6	9
15	The impact of donors on recombination mechanisms in heavily doped Ge/Si layers. Journal of Applied Physics, 2017, 121, 245701.	2.5	19
16	A self-ordered, body-centered tetragonal superlattice of SiGe nanodot growth by reduced pressure CVD. Nanotechnology, 2017, 28, 485303.	2.6	10
17	C and Si delta doping in Ge by CH ₃ SiH ₃ using reduced pressure chemical vapor deposition. Thin Solid Films, 2016, 602, 24-28.	1.8	0
18	Arsenic atomic layer doping in Si using AsH ₃ . Solid-State Electronics, 2015, 110, 29-34.	1.4	7

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19	Phosphorus atomic layer doping in Ge using RPCVD. Solid-State Electronics, 2013, 83, 25-29.	1.4	14
20	Low threading dislocation Ge on Si by combining deposition and etching. Thin Solid Films, 2012, 520, 3216-3221.	1.8	37
21	Low threading dislocation density Ge deposited on Si (100) using RPCVD. Solid-State Electronics, 2011, 60, 2-6.	1.4	114
22	B atomic layer doping of Ge. Thin Solid Films, 2010, 518, S44-S47.	1.8	15
23	Selective Polycrystalline Si and SiGe Deposition on Epitaxial Si Induced by B-Atomic Layer Doping. ECS Transactions, 2009, 16, 503-510.	0.5	3
24	Base doping and dopant profile control of SiGe npn and pnp HBTs. Applied Surface Science, 2008, 254, 6013-6016.	6.1	19
25	Atomic layer processing for doping of SiGe. Thin Solid Films, 2006, 508, 279-283.	1.8	27